

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of
Takahisa YAMAHA
Serial No.: 09/518,709
Filed: March 3, 2000



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For: MANUFACTURE METHOD FOR SEMICONDUCTOR WITH SMALL VARIATION IN MOS THRESHOLD VOLTAGE

Assistant Commissioner of Patents
Washington, D.C. 20231

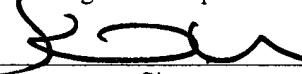
SUBMISSION

Sir:

<input checked="" type="checkbox"/>	Submitted herewith is a copy of art together with an art listing form listing the same for the convenience of the Examiner.
<input checked="" type="checkbox"/>	The Japanese Publication(s) listed on the attached art listing form was/were cited in a Japanese Office Action issued in a related application. A copy of the Office Action is attached. English-language Abstracts have been provided for the references.

I hereby certify that this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to:
Assistant Commissioner of Patents, Washington,
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Steven I. Weisburd
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Signature
March 12, 2001
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Respectfully submitted,


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SIW:sk/s/Enclosures